

Sayleap

List of Publications by Year in descending order

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6
papers

110
citations

1478505

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1872680

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g-index

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docs citations

6
times ranked

107
citing authors

#	ARTICLE	IF	CITATIONS
1	Origin of reverse leakage current path in edge-defined film-fed growth (001) $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky barrier diodes observed by high-sensitive emission microscopy. Applied Physics Letters, 2020, 117, .	3.3	34
2	Stacking faults: Origin of leakage current in halide vapor phase epitaxial (001) $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky barrier diodes. Applied Physics Letters, 2021, 118, .	3.3	29
3	Polycrystalline defectsâ€™origin of leakage currentâ€™in halide vapor phase epitaxial (001) $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky barrier diodes identified via ultrahigh sensitive emission microscopy and synchrotron X-ray topography. Applied Physics Express, 2021, 14, 036502.	2.4	21
4	Probe-induced surface defects: Origin of leakage current in halide vapor-phase epitaxial (001) $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky barrier diodes. Applied Physics Letters, 2022, 120, .	3.3	10
5	High crystal quality of vertical Bridgman and edge-defined film-fed growth $\text{In}^2\text{-Ga}_2\text{O}_3$ bulk crystals investigated using high-resolution X-ray diffraction and synchrotron X-ray topography. Japanese Journal of Applied Physics, 2022, 61, 055501.	1.5	8
6	Line-shaped defects: Origin of leakage current in halide vapor-phase epitaxial (001) $\text{In}^2\text{-Ga}_2\text{O}_3$ Schottky barrier diodes. Applied Physics Letters, 2022, 120, 122107.	3.3	8